

Data Sheet

FEATURES

0.5 Ω typical on resistance 0.8 Ω maximum on resistance at 125°C 1.65 V to 3.6 V operation Automotive temperature range: -40°C to +125°C High current carrying capability: 300 mA continuous Rail-to-rail switching operation Fast-switching times <20 ns Typical power consumption (<0.1 μ W)

APPLICATIONS

Cellular phones PDAs MP3 players Power routing Battery-powered systems PCMCIA cards Modems Audio and video signal routing Communication systems

GENERAL DESCRIPTION

The ADG836 is a low voltage complementary metal-oxide semiconductor (CMOS) device containing two independently selectable single-pole, double-throw (SPDT) switches. This device offers an ultralow on resistance of less than 0.8 Ω over the full temperature range. The ADG836 is fully specified for 3.3 V, 2.5 V, and 1.8 V supply operation.

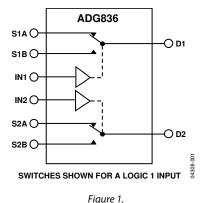
Each switch conducts equally well in both directions when on, and has an input signal range that extends to the supplies. The ADG836 exhibits break-before-make switching action.

The ADG836 is available in a 10-lead MSOP and in a 3 mm \times 3 mm 12-lead LFCSP.

0.5 Ω CMOS, 1.65 V TO 3.6 V, Dual SPDT/2:1 MUX

ADG836

FUNCTIONAL BLOCK DIAGRAM



PRODUCT HIGHLIGHTS

- 1. $<0.8 \Omega$ over full temperature range of -40° C to $+125^{\circ}$ C.
- 2. Single 1.65 V to 3.6 V operation.
- 3. Compatible with 1.8 V CMOS logic.
- 4. High current handling capability (300 mA continuous current at 3.3 V).
- Low total harmonic distortion plus noise (THD + N) (0.02% typical).
- 6. $3 \text{ mm} \times 3 \text{ mm}$ LFCSP and 10-lead MSOP.

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REVISION HISTORY

8/2020—Rev. B to Rev. C	
Changes to Table 1 3	3
Changes to Table 2 4	ł
Changes to Table 3	;

6/2016—Rev. A to Rev. B

Changed CP-12-1 to CP-12-4	Throughout
Changes to Figure 3 and Table 6	
Added Terminology Section	
Updated Outline Dimensions	
Changes to Ordering Guide	

4/2005—Rev. 0 to Rev. A	
Updated Format	Universal
Changes to Table 1	3
Changes to Table 2	4
Changes to Table 3	
Changes to Ordering Guide	

8/2003—Revision 0: Initial Version

SPECIFICATIONS

 $V_{DD} = 2.7 V$ to 3.6 V, GND = 0 V, unless otherwise noted. The temperature range for the Y version is -40° C to $+125^{\circ}$ C.

Table 1.	1			T	
Parameter	+25°C	-40°C to +85°C	-40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			0 V to V _{DD}	V	
On Resistance (R _{ON})	0.5			Ωtyp	$V_{\text{DD}}=2.7 \text{ V}, V_{\text{S}}=0 \text{ V} \text{ to } V_{\text{DD}}, I_{\text{S}}=100 \text{ mA};$ Figure 19
	0.75	0.85	0.9	Ωmax	
On-Resistance Match Between	0.04			Ωtyp	$V_{DD} = 2.7 \text{ V}, V_S = 0.65 \text{ V}, I_S = 100 \text{ mA}$
Channels (ΔR _{ON})	0.095	0.095	0.1	Ωmax	
On-Resistance Flatness (R _{FLAT (ON)})	0.1			Ωtyp	$V_{DD} = 2.7 \text{ V}, \text{ V}_{S} = 0 \text{ V} \text{ to } \text{V}_{DD}$
	0.18	0.18	0.19	Ωmax	ls = 100 mA
LEAKAGE CURRENTS					$V_{DD} = 3.6 V$
Source Off Leakage Is (OFF)	±0.2			nA typ	$V_{S} = 0.6 \text{ V}/3.3 \text{ V}, V_{D} = 3.3 \text{ V}/0.6 \text{ V};$ Figure 20
Channel On Leakage I _D , I _s (ON)	±0.2			nA typ	$V_{s} = V_{D} = 0.6 V \text{ or } 3.3 V;$ Figure 21
DIGITAL INPUTS					
Input High Voltage, V _{INH}			2	V min	
Input Low Voltage, V _{INL}			0.8	V max	
Input Current					
IINL OF INH	0.005			μA typ	$V_{IN} = V_{INL} \text{ or } V_{INH}$
			±0.1	µA max	
C _{IN} , Digital Input Capacitance	4			pF typ	
DYNAMIC CHARACTERISTICS ¹					
t _{on}	21			ns typ	$R_L = 50 \Omega, C_L = 35 pF$
	26	28	29	ns max	Vs = 1.5 V/0 V; Figure 22
t _{OFF}	4			ns typ	$R_L = 50 \Omega, C_L = 35 pF$
	7	8	9	ns max	Vs = 1.5 V; Figure 22
Break-Before-Make Time Delay (t _{BBM})	17			ns typ	$R_L = 50 \Omega, C_L = 35 pF$
			5	ns min	$V_{S1} = V_{S2} = 1.5 V$; Figure 23
Charge Injection	40			pC typ	$V_s = 1.5 V, R_s = 0 \Omega, C_L = 1 nF;$ Figure 24
Off Isolation	-67			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$; Figure 25
Channel-to-Channel Crosstalk	-90			dB typ	S1A to S2A/S1B to S2B, $R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 \text{ kHz}$; Figure 28
	-67			dB typ	S1A to S1B/S2A to S2B, $R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$; Figure 27
Total Harmonic Distortion Plus Noise (THD + N)	0.02			%	$\label{eq:RL} \begin{array}{l} R_{\text{L}} = 32 \; \Omega, f = 20 \; \text{Hz} \; \text{to} \; 20 \; \text{kHz}, \\ V_{\text{S}} = 2 \; V \; p\text{-}p \end{array}$
Insertion Loss	-0.05			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$; Figure 26
–3 dB Bandwidth	57			MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; Figure 26
C _s (OFF)	25			pF typ	
C _D , C _S (ON)	75			pF typ	
POWER REQUIREMENTS					V _{DD} = 3.6 V
ldd	0.003			μA typ	Digital inputs = 0 V or 3.6 V
		1	4	µA max	

¹ Guaranteed by design, not subject to production test.

 V_{DD} = 2.5 V ± 0.2 V, GND = 0 V, unless otherwise noted. The temperature range for the Y version is -40°C to +125°C.

Table 2.

Parameter	+25°C	-40°C to +85°C	-40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			0 V to V _{DD}	V	
On Resistance (R _{ON})	0.65			Ωtyp	$V_{DD} = 2.3 V$, $V_s = 0 V$ to V_{DD} , $I_s = 100 mA$; Figure 19
	0.84	0.92	1.0	Ωmax	_
On-Resistance Match Between	0.04			Ωtyp	$V_{DD} = 2.3 V, V_s = 0.7 V, I_s = 100 mA$
Channels (ΔR _{ON})	0.1	0.1	0.105	Ωmax	
On-Resistance Flatness (R _{FLAT (ON)})	0.16			Ωtyp	$V_{DD} = 2.3 \text{ V}, \text{ V}_{\text{S}} = 0 \text{ V} \text{ to } \text{V}_{DD}, \text{ I}_{\text{S}} = 100 \text{ mA}$
	0.25	0.25	0.26	Ωmax	
LEAKAGE CURRENTS					$V_{DD} = 2.7 \text{ V}$
Source Off Leakage Is (OFF)	±0.2			nA typ	$V_{\rm S} = 0.6 \text{ V}/2.4 \text{ V}, V_{\rm D} = 2.4 \text{ V}/0.6 \text{ V};$ Figure 20
Channel On Leakage I _D , I _S (ON)	±0.2			nA typ	$V_{s} = V_{D} = 0.6 V \text{ or } 2.4 V;$ Figure 21
DIGITAL INPUTS					
Input High Voltage, VINH			1.7	V min	
Input Low Voltage, VINL			0.7	V max	
Input Current					
I _{INL} or I _{INH}	0.005			μA typ	$V_{IN} = V_{INL}$ or V_{INH}
			±0.1	µA max	
C _{IN} , Digital Input Capacitance	4			pF typ	
DYNAMIC CHARACTERISTICS ¹					
ton	23			ns typ	$R_L = 50 \Omega, C_L = 35 pF$
	29	30	31	ns max	Vs = 1.5 V/0 V; Figure 22
toff	5			ns typ	$R_L = 50 \Omega$, $C_L = 35 pF$
	7	8	9	ns max	$V_{s} = 1.5 V;$ Figure 22
Break-before-Make Time Delay (t _{BBM})	17			ns typ	$R_L = 50 \Omega$, $C_L = 35 pF$
			5	ns min	$V_{s_1} = V_{s_2} = 1.5 V$; Figure 23
Charge Injection	30			pC typ	$V_s = 1.25 V$, $R_s = 0 \Omega$, $C_L = 1 nF$; Figure 24
Off Isolation	-67			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$; Figure 25
Channel-to-Channel Crosstalk	-90			dB typ	S1A to S2A/S1B to S2B, $R_L = 50 \Omega$, $C_L = 5 pF$,
					f = 100 kHz; Figure 28
	-67			dB typ	S1A to S1B/S2A to S2B, $R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 \text{ kHz}$; Figure 27
Total Harmonic Distortion Plus Noise (THD + N)	0.022			%	$R_L = 32 \Omega$, $f = 20$ Hz to 20 kHz, $V_S = 1.5$ V p-p
Insertion Loss	-0.06			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$; Figure 26
–3 dB Bandwidth	57			MHz typ	
Cs (OFF)	25			pF typ	
C _D , C _s (ON)	75			pF typ	
POWER REQUIREMENTS					V _{DD} = 2.7 V
I _{DD}	0.003			μA typ	Digital inputs = 0 V or 2.7 V
		1	4	µA max	

¹ Guaranteed by design, not subject to production test.

Data Sheet

 V_{DD} = 1.65 V ± 1.95 V, GND = 0 V, unless otherwise noted. The temperature range for the Y version is -40°C to +125°C.

Parameter	+25°C	-40°C to +85°C	-40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			0 V to V _{DD}	V	
On Resistance (R _{ON})	1			Ω typ	$V_{DD} = 1.8 V$, $V_{S} = 0 V$ to V_{DD} , $I_{S} = 100 m$ A; Figure 19
	1.6	2.4	2.4	Ωmax	_
	2.7	4.2	4.2	Ωmax	$V_{\text{DD}} = 1.65 \text{ V}, \text{V}_{\text{S}} = 0 \text{ V} \text{ to } \text{V}_{\text{DD}}, \text{I}_{\text{S}} = 100 \text{ mA}$ Figure 19
On-Resistance Match Between	0.1			Ωtyp	$V_{DD} = 1.65 \text{ V}, V_S = 0.7 \text{ V}, I_S = 100 \text{ mA}$
Channels (ΔR _{ON})					
LEAKAGE CURRENTS					$V_{DD} = 1.95 V$
Source Off Leakage I_S (OFF)	±0.2			nA typ	$V_{s} = 0.6 \text{ V}/1.65 \text{ V}, V_{D} = 1.65 \text{ V}/0.6 \text{ V};$ Figure 20
Channel On Leakage ID, Is (ON)	±0.2			nA typ	$V_{s} = V_{D} = 0.6 V \text{ or } 1.65 V$; Figure 21
DIGITAL INPUTS					
Input High Voltage, V _{INH}			0.65 V _{DD}	V min	
Input Low Voltage, V _{INL}			0.35 V _{DD}	V max	
Input Current					
I _{INL} or I _{INH}	0.005			μA typ	$V_{IN} = V_{INL} \text{ or } V_{INH}$
			±0.1	µA max	
C _{IN} , Digital Input Capacitance	4			pF typ	
DYNAMIC CHARACTERISTICS ¹					
t _{ON}	28			ns typ	$R_L = 50 \Omega$, $C_L = 35 pF$
	37	38	39	ns max	Vs = 1.5 V/0 V; Figure 22
toff	7			ns typ	$R_L = 50 \Omega$, $C_L = 35 pF$
	9	10	11	ns max	V _s = 1.5 V; Figure 22
Break-Before-Make Time Delay (t _{BBM})	21			ns typ	$R_L = 50 \Omega, C_L = 35 pF$
			5	ns min	$V_{S1} = V_{S2} = 1 V$; Figure 23
Charge Injection	20			pC typ	$V_s = 1 V, R_s = 0 V, C_L = 1 nF;$ Figure 24
Off Isolation	-67			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$; Figure 25
Channel-to-Channel Crosstalk	-90			dB typ	S1A to S2A/S1B to S2B; $R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$; Figure 28
	-67			dB typ	S1A to S1B/S2A to S2B; $R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$;
Total Harmonic Distortion (THD)	0.14			%	Figure 27 $R_L = 32 \Omega$, f = 20 Hz to 20 kHz, $V_S = 1.2 V p-p$
Insertion Loss	-0.08			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$; Figure 26
–3 dB Bandwidth	57			MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; Figure 26
Cs (OFF)	25			pF typ	, -L - p.,
$C_{\rm D}, C_{\rm S}$ (ON)	75			pF typ	
POWER REQUIREMENTS				177 - 7 P	V _{DD} = 1.95 V
IDD	0.003			μA typ	Digital inputs = 0 V or 1.95 V
		1.0	4	μA max	

¹ Guaranteed by design, not subject to production test.

ABSOLUTE MAXIMUM RATINGS

 $T_A = 25^{\circ}C$, unless otherwise noted.

Table 4.

Table 4.				
Parameter	Rating			
V _{DD} to GND	–0.3 V to +4.6 V			
Analog Inputs ¹	-0.3 V to V _{DD} + 0.3 V			
Digital Inputs ¹	–0.3 V to 4.6 V or 10 mA, whichever occurs first			
Peak Current, S or D				
3.3 V Operation	500 mA			
2.5 V Operation	460 mA			
1.8 V Operation	420 mA (pulsed at 1ms, 10% duty cycle max)			
Continuous Current, S or D				
3.3 V Operation	300 mA			
2.5 V Operation	275 mA			
1.8 V Operation	250 mA			
Operating Temperature Range				
Automotive (Y Version)	-40°C to +125°C			
Storage Temperature Range	–65°C to +150°C			
Junction Temperature	150°C			
Thermal Impedance				
MSOP				
Θ_{JA}	206°C/W			
θ」ϲ	44°C/W			
LFCSP				
θ_{JA} (3-Layer Board)	61.1°C/W			
IR Reflow, Peak Temperature <20 sec	235°C			

¹ Overvoltages at IN, S, or D are clamped by internal diodes. Current should be limited to the maximum ratings given.

Stresses at or above those listed under Absolute Maximum Ratings may cause permanent damage to the product. This is a stress rating only; functional operation of the product at these or any other conditions above those indicated in the operational section of this specification is not implied. Operation beyond the maximum operating conditions for extended periods may affect product reliability.

Only one absolute maximum rating may be applied at any one time.

Table 5. Truth Table

Logic	Switch A	Switch B
0	Off	On
1	On	Off

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

PIN CONFIGURATIONS AND FUNCTION DESCRIPTIONS

04308-002

IN1 1 S1A 2 GND 3 S2A 4 IN2 5 ADG836 TOP VIEW (Not to Scale)	10 D1 9 S1B 8 V _{DD} 7 S2B 6 D2
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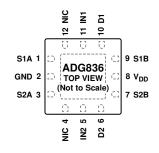


Figure 2. 10-Lead MSOP Pin Configuration (RM-10)

Table 6. Pin Function Descriptions

Figure 3. 12-Lead LFCSP Pin Configuration (CP-12-4)

Pin No.					
MSOP	LFCSP	Mnemonic	Description		
1, 5	11, 5	IN1, IN2	Logic Control Inputs.		
2, 4, 7, 9	1, 3, 7, 9	S1A, S2A, S2B, S1B	Source Terminals. Can be inputs or outputs.		
3	2	GND	Ground (0 V) Reference.		
6, 10	6, 10	D2, D1	Drain Terminals. Can be inputs or outputs.		
8	8	V _{DD}	Most Positive Power Supply Potential.		
Not applicable	4, 12	NIC	No Internal Connection.		
Not applicable	0	EPAD	Exposed Pad. It is recommended that the exposed pad be thermally connected to a copper plane for enhanced thermal performance. The exposed pad should be grounded as wel		

TYPICAL PERFORMANCE CHARACTERISTICS

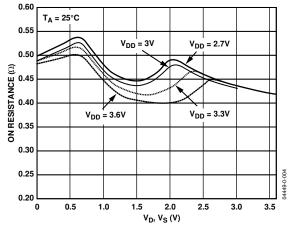


Figure 4. On Resistance vs. V_D (Vs), $V_{DD} = 2.7 V$ to 3.6 V

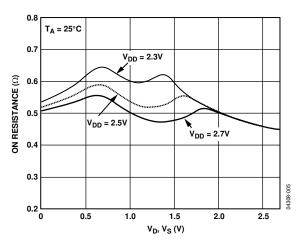


Figure 5. On Resistance vs. V_D (V_S), V_{DD} = 2.5 V to 0.2 V

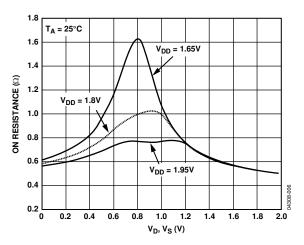


Figure 6. On Resistance vs. V_D (V_s), $V_{DD} = 1.8 \pm 3.6$

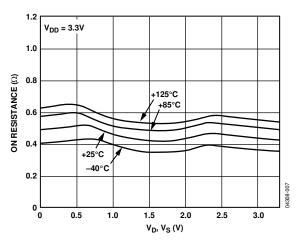


Figure 7. On Resistance vs. V_D (V_s) for Different Temperatures, 3.3 V

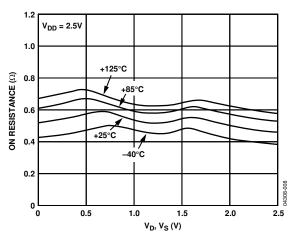


Figure 8. On Resistance vs. V_D (V_s) for Different Temperatures, 2.5 V

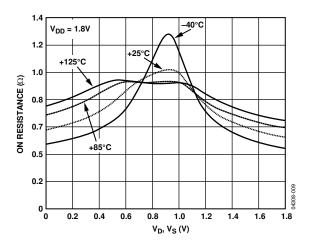


Figure 9. On Resistance vs. V_D (Vs) for Different Temperatures, 1.8 V

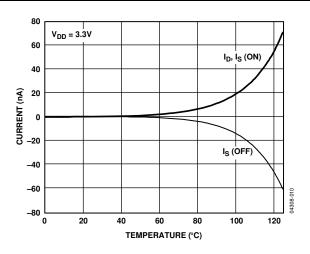


Figure 10. Leakage Current vs. Temperature, 3.3 V

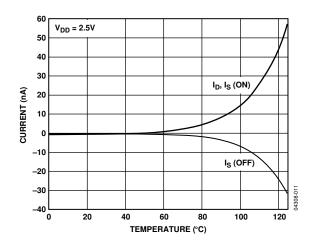


Figure 11. Leakage Current vs. Temperature, 2.5 V

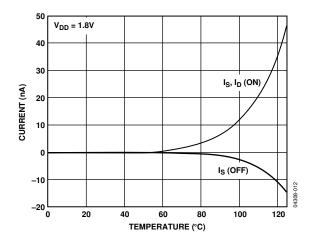


Figure 12. Leakage Current vs. Temperature, 1.8 V

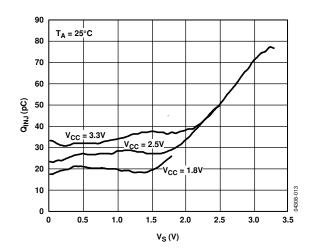
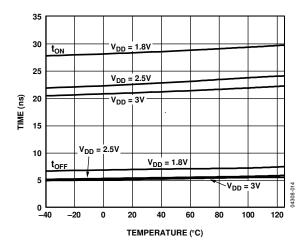


Figure 13. Charge Injection vs. Source Voltage





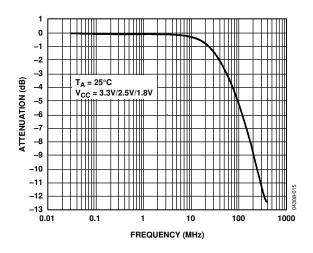


Figure 15. Bandwidth

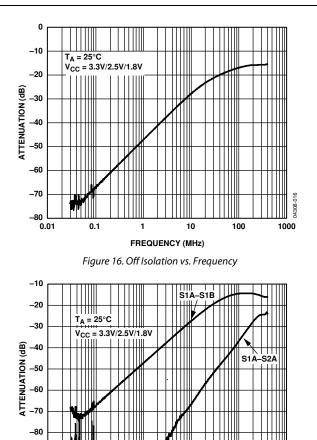
-90

-100 L 0.01

0.1

1

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FREQUENCY (MHz) Figure 17. Crosstalk vs. Frequency

100

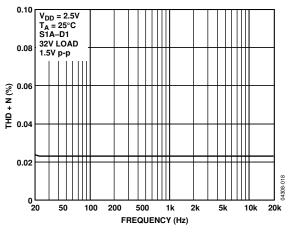
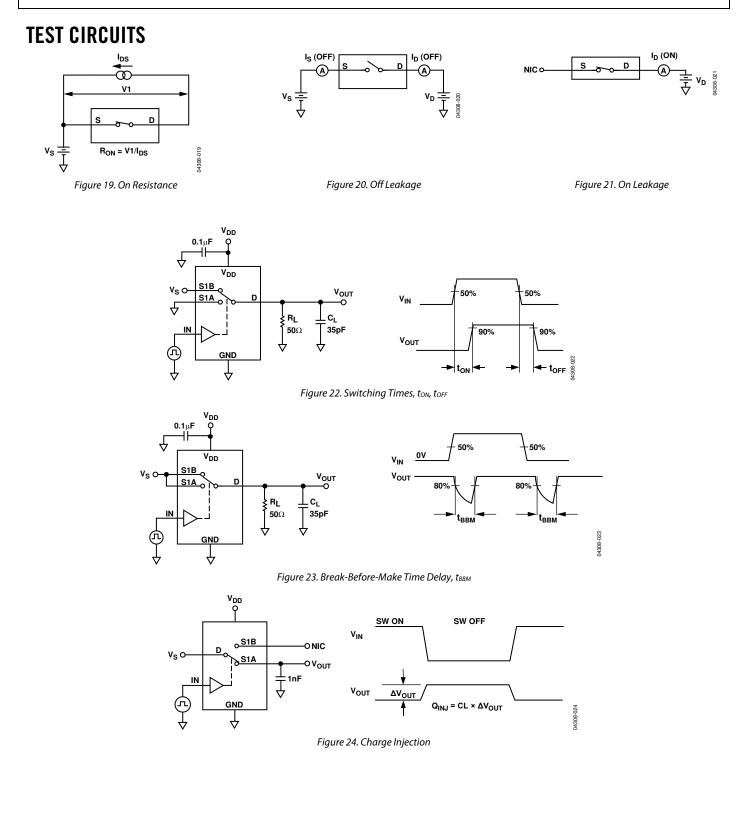


Figure 18. THD + N

04308-017

1000



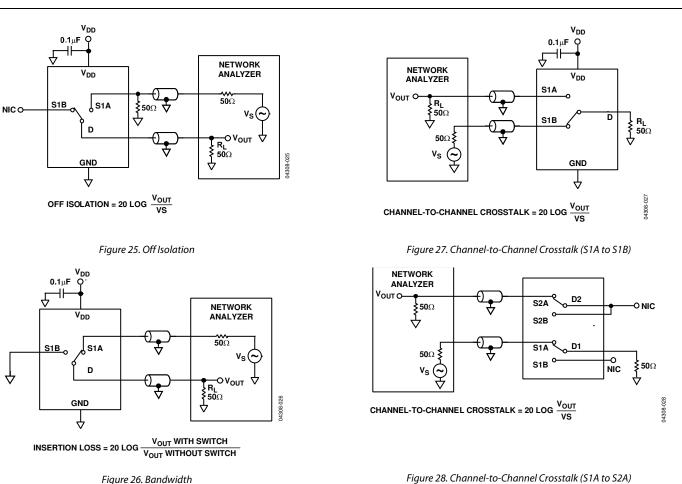


Figure 26. Bandwidth

TERMINOLOGY

IDD Positive supply current.

V_D (Vs) Analog voltage on Terminal D and Terminal S.

R_{ON} Ohmic resistance between Terminal D and Terminal S.

$R_{FLAT (ON)}$

Flatness is defined as the difference between the maximum and minimum value of on resistance as measured over the specified analog signal range.

 ΔR_{ON} On-resistance match between any two channels.

Is (OFF) Source leakage current with the switch off.

I_D (OFF) Drain leakage current with the switch off.

I_D, I_s (ON) Channel leakage current with the switch on.

V_{INL} Maximum input voltage for Logic 0.

V_{INH} Minimum input voltage for Logic 1.

I_{INL} (I_{INH}) Input current of the digital input.

Cs (OFF)

Off switch source capacitance. Measured with reference to ground.

 C_D (OFF) Off switch drain capacitance. Measured with reference to ground. C_D, C_s (ON) On switch capacitance. Measured with reference to ground.

C_{IN} Digital input capacitance.

 t_{ON} Delay time between the 50% and the 90% points of the digital input and switch on condition.

 $t_{\rm OFF}$ Delay time between the 50% and the 90% points of the digital input and switch off condition.

t_{BBM} On or off time measured between the 80% points of both switches when switching from one to another.

Charge Injection A measure of the glitch impulse transferred from the digital input to the analog output during on-off switching.

Off Isolation A measure of unwanted signal coupling through an off switch.

Crosstalk A measure of unwanted signal, which is coupled through from one channel to another as a result of parasitic capacitance.

-3 dB Bandwidth The frequency at which the output is attenuated by 3 dB.

On Response The frequency response of the on switch.

Insertion Loss The loss due to the on resistance of the switch.

Total Harmonic Distortion Plus Noise (THD + N) The ratio of the harmonics amplitude plus the noise of a signal to the fundamental.

OUTLINE DIMENSIONS

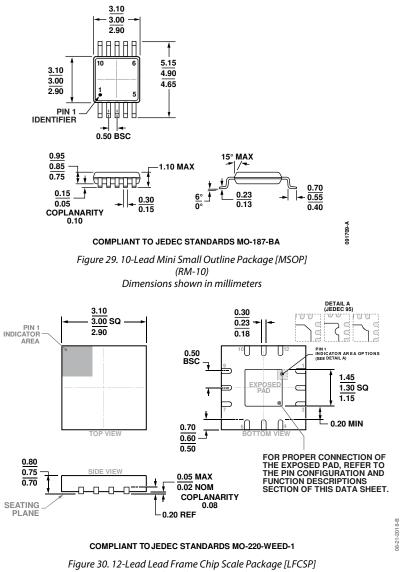


Figure 30. 12-Lead Lead Frame Chip Scale Package [LFCSP] 3 mm x 3 mm Body and 0.75 mm Package Height (CP-12-4) Dimensions shown in millimeters

ORDERING GUIDE

Model ¹	Temperature Range	Package Description	Package Option	Branding ²
ADG836YRM	-40°C to +125°C	10-Lead Mini Small Outline Package [MSOP]	RM-10	S9A
ADG836YRMZ	-40°C to +125°C	10-Lead Mini Small Outline Package [MSOP]	RM-10	S05
ADG836YRMZ-REEL	-40°C to +125°C	10-Lead Mini Small Outline Package [MSOP]	RM-10	S05
ADG836YRMZ-REEL7	-40°C to +125°C	10-Lead Mini Small Outline Package [MSOP]	RM-10	S05
ADG836YCPZ-REEL7	-40°C to +125°C	12-Lead Lead Frame Chip Scale Package [LFCSP]	CP-12-4	S05

 1 Z = RoHS Compliant Part.

² Branding on this package is limited to three characters due to space constraints.

NOTES

Data Sheet

NOTES



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